Quad 2-input NAND gate

Rev. 1 — 16 April 2013

**Product data sheet** 

## 1. General description

The 74AHC00-Q100; 74AHCT00-Q100 is a high-speed Si-gate CMOS device and is pin compatible with Low-power Schottky TTL (LSTTL). It is specified in compliance with JEDEC standard No. JESD7-A.

The 74AHC00-Q100; 74AHCT00-Q100 provides the quad 2-input NAND function.

This product has been qualified to the Automotive Electronics Council (AEC) standard Q100 (Grade 1) and is suitable for use in automotive applications.

## 2. Features and benefits

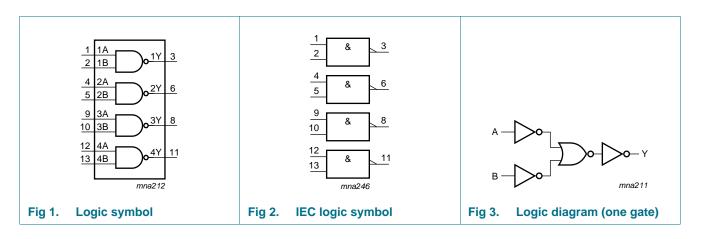
- Automotive product qualification in accordance with AEC-Q100 (Grade 1)
  - Specified from –40 °C to +85 °C and from –40 °C to +125 °C
- Balanced propagation delays
- All inputs have Schmitt-trigger actions
- Inputs accept voltages higher than V<sub>CC</sub>
- Input levels:
  - For 74AHC00-Q100: CMOS level
  - For 74AHCT00-Q100: TTL level
- ESD protection:
  - ◆ MIL-STD-883, method 3015 exceeds 2000 V
  - HBM JESD22-A114F exceeds 2000 V
  - MM JESD22-A115-A exceeds 200 V (C = 200 pF, R = 0 Ω)
- Multiple package options



## 3. Ordering information

Table 1. Ordering i	nformation			
Type number	Package			
	Temperature range	Name	Description	Version
74AHC00-Q100				
74AHC00D-Q100	–40 °C to +125 °C	SO14	plastic small outline package; 14 leads; body width 3.9 mm	SOT108-1
74AHC00PW-Q100	–40 °C to +125 °C	TSSOP14	plastic thin shrink small outline package; 14 leads; body width 4.4 mm	SOT402-1
74AHC00BQ-Q100	–40 °C to +125 °C	DHVQFN14	plastic dual in-line compatible thermal enhanced very thin quad flat package; no leads; 14 terminals; body 2.5 $\times$ 3 $\times$ 0.85 mm	SOT762-1
74AHCT00-Q100				
74AHCT00D-Q100	–40 °C to +125 °C	SO14	plastic small outline package; 14 leads; body width 3.9 mm	SOT108-1
74AHCT00PW-Q100	–40 °C to +125 °C	TSSOP14	plastic thin shrink small outline package; 14 leads; body width 4.4 mm	SOT402-1
74AHCT00BQ-Q100	–40 °C to +125 °C	DHVQFN14	plastic dual in-line compatible thermal enhanced very thin quad flat package; no leads; 14 terminals; body 2.5 $\times$ 3 $\times$ 0.85 mm	SOT762-1

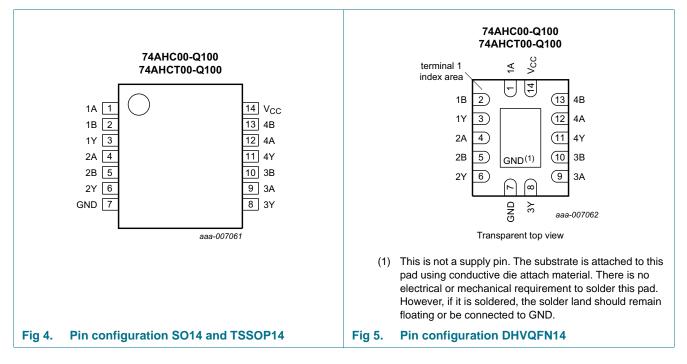
## 4. Functional diagram



**Quad 2-input NAND gate** 

## 5. Pinning information

### 5.1 Pinning



### 5.2 Pin description

Table 2.	Pin description	
Symbol	Pin	Description
1A	1	data input
1B	2	data input
1Y	3	data output
2A	4	data input
2B	5	data input
2Y	6	data output
GND	7	ground (0 V)
3Y	8	data output
3A	9	data input
3B	10	data input
4Y	11	data output
4A	12	data input
4B	13	data input
V <sub>CC</sub>	14	supply voltage

## 6. Functional description

Table 3.	Function selection <sup>[1]</sup>		
Input			Output
nA		nB	nY
L		x	Н
Х		L	Н
Н		Н	L

[1] H = HIGH voltage level; L = LOW voltage level; X = don't care.

## 7. Limiting values

#### Table 4.Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134). Voltages are referenced to GND (ground = 0 V).

Symbol	Parameter	Conditions	Min	Max	Unit
V <sub>CC</sub>	supply voltage		-0.5	+7.0	V
VI	input voltage		-0.5	+7.0	V
I <sub>IK</sub>	input clamping current	V <sub>1</sub> < -0.5 V	<u>[1]</u> –20	-	mA
Ι <sub>ΟΚ</sub>	output clamping current	$V_{\rm O}$ < –0.5 V or $V_{\rm O}$ > $V_{\rm CC}$ + 0.5 V	<u>[1]</u> –20	+20	mA
lo	output current	$V_{O} = -0.5 \text{ V}$ to ( $V_{CC} + 0.5 \text{ V}$ )	-25	+25	mA
I <sub>CC</sub>	supply current		-	+75	mA
I <sub>GND</sub>	ground current		-75	-	mA
T <sub>stg</sub>	storage temperature		-65	+150	°C
P <sub>tot</sub>	total power dissipation	$T_{amb} = -40 \ ^{\circ}C \ to \ +125 \ ^{\circ}C$	[2] _	500	mW

[1] The input and output voltage ratings may be exceeded if the input and output current ratings are observed.

[2] For SO14 packages: above 70 °C the value of P<sub>tot</sub> derates linearly at 8 mW/K. For TSSOP14 packages: above 60 °C the value of P<sub>tot</sub> derates linearly at 5.5 mW/K. For DHVQFN14 packages: above 60 °C the value of P<sub>tot</sub> derates linearly at 4.5 mW/K.

## 8. Recommended operating conditions

Table 5.	Operating conditions					
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
74AHC00-	Q100					
V <sub>CC</sub>	supply voltage		2.0	5.0	5.5	V
VI	input voltage		0	-	5.5	V
Vo	output voltage		0	-	V <sub>CC</sub>	V
T <sub>amb</sub>	ambient temperature		-40	+25	+125	°C
$\Delta t / \Delta V$	input transition rise and fall rate	$V_{CC}$ = 3.0 V to 3.6 V	-	-	100	ns/V
		$V_{CC}$ = 4.5 V to 5.5 V	-	-	20	ns/V

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Table 5.	<b>Operating conditions</b> com	tinued				
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
74AHCT0	0-Q100					
V <sub>CC</sub>	supply voltage		4.5	5.0	5.5	V
VI	input voltage		0	-	5.5	V
Vo	output voltage		0	-	$V_{CC}$	V
T <sub>amb</sub>	ambient temperature		-40	+25	+125	°C
$\Delta t / \Delta V$	input transition rise and	fall rate $V_{CC} = 4.5 \text{ V}$ to 5.5 V	-	-	20	ns/V

## 9. Static characteristics

#### Table 6. Static characteristics

At recommended operating conditions; voltages are referenced to GND (ground = 0 V).

Symbol	Parameter	Conditions		25 °C		–40 °C t	o +85 °C	–40 °C to	o +125 ℃	Unit
			Min	Тур	Max	Min	Max	Min	Max	
74AHC0	0-Q100									
V <sub>IH</sub>	HIGH-level input	V <sub>CC</sub> = 2.0 V	1.5	-	-	1.5	-	1.5	-	V
	voltage	V <sub>CC</sub> = 3.0 V	2.1	-	-	2.1	-	2.1	-	V
		V <sub>CC</sub> = 5.5 V	3.85	-	-	3.85	-	3.85	-	V
V <sub>IL</sub>		V <sub>CC</sub> = 2.0 V	-	-	0.5	-	0.5	-	0.5	V
	voltage	V <sub>CC</sub> = 3.0 V	-	-	0.9	-	0.9	-	0.9	V
		V <sub>CC</sub> = 5.5 V	-	-	1.65	-	1.65	-	1.65	V
V <sub>ОН</sub>	HIGH-level output voltage	$V_{I} = V_{IH} \text{ or } V_{IL}$								
		$I_{O}$ = -50 $\mu$ A; $V_{CC}$ = 2.0 V	1.9	2.0	-	1.9	-	1.9	-	V
		$I_{O} = -50 \ \mu A; \ V_{CC} = 3.0 \ V$	2.9	3.0	-	2.9	-	2.9	-	V
		$I_{O}$ = -50 $\mu$ A; $V_{CC}$ = 4.5 V	4.4	4.5	-	4.4	-	4.4	-	V
		$I_0 = -4.0 \text{ mA}; V_{CC} = 3.0 \text{ V}$	2.58	-	-	2.48	-	2.40	-	V
		$I_0 = -8.0 \text{ mA}; V_{CC} = 4.5 \text{ V}$	3.94	-	-	3.80	-	3.70	-	V
V <sub>OL</sub>	LOW-level output	$V_{I} = V_{IH} \text{ or } V_{IL}$								
	voltage	$I_0 = 50 \ \mu A; \ V_{CC} = 2.0 \ V$	-	0	0.1	-	0.1	-	0.1	V
		$I_0 = 50 \ \mu A; \ V_{CC} = 3.0 \ V$	-	0	0.1	-	0.1	-	0.1	V
		$I_0 = 50 \ \mu A; \ V_{CC} = 4.5 \ V$	-	0	0.1	-	0.1	-	0.1	V
		$I_{O}$ = 4.0 mA; $V_{CC}$ = 3.0 V	-	-	0.36	-	0.44	-	0.55	V
		$I_0 = 8.0 \text{ mA}; V_{CC} = 4.5 \text{ V}$	-	-	0.36	-	0.44	-	0.55	V
I	input leakage current	V <sub>I</sub> = 5.5 V or GND; V <sub>CC</sub> = 0 V to 5.5 V	-	-	0.1	-	1.0	-	2.0	μA
I <sub>CC</sub>	supply current		-	-	2.0	-	20	-	40	μΑ
CI	input capacitance	$V_I = V_{CC}$ or GND	-	3.0	10	-	10	-	10	pF

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Symbol	Parameter	Conditions		25 °C		–40 °C t	o +85 °C	–40 °C to	+125 °C	Unit
			Min	Тур	Max	Min	Max	Min	Max	
74AHCT	00-Q100									
V <sub>IH</sub>	HIGH-level input voltage	$V_{CC}$ = 4.5 V to 5.5 V	2.0	-	-	2.0	-	2.0	-	V
V <sub>IL</sub>	LOW-level input voltage	$V_{CC}$ = 4.5 V to 5.5 V	-	-	0.8	-	0.8	-	0.8	V
-011	HIGH-level	$V_{I}$ = $V_{IH}$ or $V_{IL};V_{CC}$ = 4.5 V								
	output voltage	I <sub>O</sub> = -50 μA	4.4	4.5	-	4.4	-	4.4	-	V
		I <sub>O</sub> = -8.0 mA	3.94	-	-	3.80	-	3.70	-	V
V <sub>OL</sub>	LOW-level output	$V_{I}$ = $V_{IH}$ or $V_{IL};V_{CC}$ = 4.5 V								
	voltage	I <sub>O</sub> = 50 μA	-	0	0.1	-	0.1	-	0.1	V
		l <sub>O</sub> = 8.0 mA	-	-	0.36	-	0.44	-	0.55	V
l <sub>l</sub>	input leakage current	$V_I = 5.5 V \text{ or GND};$ $V_{CC} = 0 V \text{ to } 5.5 V$	-	-	0.1	-	1.0	-	2.0	μA
I <sub>CC</sub>	supply current		-	-	2.0	-	20	-	40	μA
ΔI <sub>CC</sub>	additional supply current	per input pin; $V_I = V_{CC} - 2.1 \text{ V};$ other pins at $V_{CC}$ or GND; $I_O = 0 \text{ A}; V_{CC} = 4.5 \text{ V}$ to 5.5 V	-	-	1.35	-	1.5	-	1.5	mA
CI	input capacitance	$V_{I} = V_{CC}$ or GND	-	3.0	10	-	10	-	10	pF

### Table 6. Static characteristics ...continued

At recommended operating conditions; voltages are referenced to GND (ground = 0 V).

## **10.** Dynamic characteristics

#### Table 7. Dynamic characteristics

Voltages are referenced to GND (ground = 0 V); for test circuit see Figure 7.

Symbol	Parameter	Conditions		25 °C		–40 °C t	o +85 °C	–40 °C te	o +125 °C	Unit
			Min	Typ <mark>[1]</mark>	Max	Min	Max	Min	Max	
74AHC0	D-Q100			•						
	propagation delay	nA, nB to nY; see Figure 6	2]							
		$V_{CC} = 3.0 \text{ V} \text{ to } 3.6 \text{ V}$								
		C <sub>L</sub> = 15 pF	-	4.5	7.9	1.0	9.5	1.0	10.0	ns
		C <sub>L</sub> = 50 pF	-	6.0	11.4	1.0	13.0	1.0	14.5	ns
		$V_{CC}$ = 4.5 V to 5.5 V								
		C <sub>L</sub> = 15 pF	-	3.2	5.5	1.0	6.5	1.0	7.0	ns
		C <sub>L</sub> = 50 pF	-	4.5	7.5	1.0	8.5	1.0	9.5	ns
C <sub>PD</sub>	power dissipation capacitance	$\label{eq:CL} \begin{split} &C_L = 50 \text{ pF; } f_i = 1 \text{ MHz;} \\ &V_i = \text{GND to } V_{\text{CC}} \end{split}$	<u>3]</u>	7.0	-	-	-	-	-	pF

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Symbol	Parameter	Conditions		25 °C		–40 °C to +85 °C		–40 °C to	o +125 °C	Unit	
				Min	Typ[1]	Max	Min	Max	Min	Max	
74AHCT	00-Q100										
P	propagation delay	nA, nB to nY; see <u>Figure 6</u>	[2]								
		$V_{CC}$ = 4.5 V to 5.5 V									
		C <sub>L</sub> = 15 pF		-	3.3	6.9	1.0	8.0	1.0	9.0	ns
		C <sub>L</sub> = 50 pF		-	4.5	7.9	1.0	9.0	1.0	10.0	ns
C <sub>PD</sub>	power dissipation capacitance	$C_L$ = 50 pF; f <sub>i</sub> = 1 MHz; V <sub>I</sub> = GND to V <sub>CC</sub>	<u>[3]</u>	-	7.0	-	-	-	-	-	pF

#### Table 7. Dynamic characteristics ...continued

Voltages are referenced to GND (ground = 0 V); for test circuit see Figure 7.

[1] Typical values are measured at nominal supply voltage (V<sub>CC</sub> = 3.3 V and V<sub>CC</sub> = 5.0 V).

[3]  $C_{PD}$  is used to determine the dynamic power dissipation (P<sub>D</sub> in  $\mu$ W).

 $P_{D} = C_{PD} \times V_{CC}^{2} \times f_{i} \times N + \Sigma (C_{L} \times V_{CC}^{2} \times f_{o}) \text{ where:}$ 

 $f_i$  = input frequency in MHz;

 $f_o = output frequency in MHz;$ 

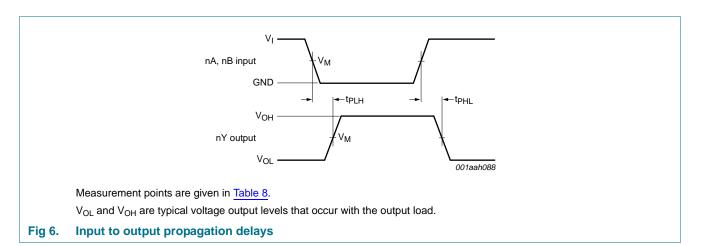
 $C_L$  = output load capacitance in pF;

 $V_{CC}$  = supply voltage in V;

N = number of inputs switching;

 $\Sigma(C_L \times V_{CC}^2 \times f_o)$  = sum of the outputs.

## 11. Waveforms



#### Table 8.Measurement points

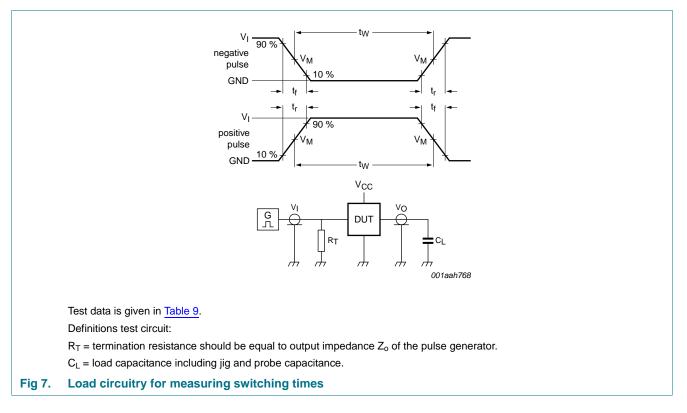
Туре	Input	Output		
	V <sub>M</sub>	V <sub>M</sub>		
74AHC00-Q100	$0.5  imes V_{CC}$	$0.5  imes V_{CC}$		
74AHCT00-Q100	1.5 V	$0.5 \times V_{CC}$		

<sup>[2]</sup>  $t_{pd}$  is the same as  $t_{PLH}$  and  $t_{PHL}$ .

### **NXP Semiconductors**

# 74AHC00-Q100; 74AHCT00-Q100

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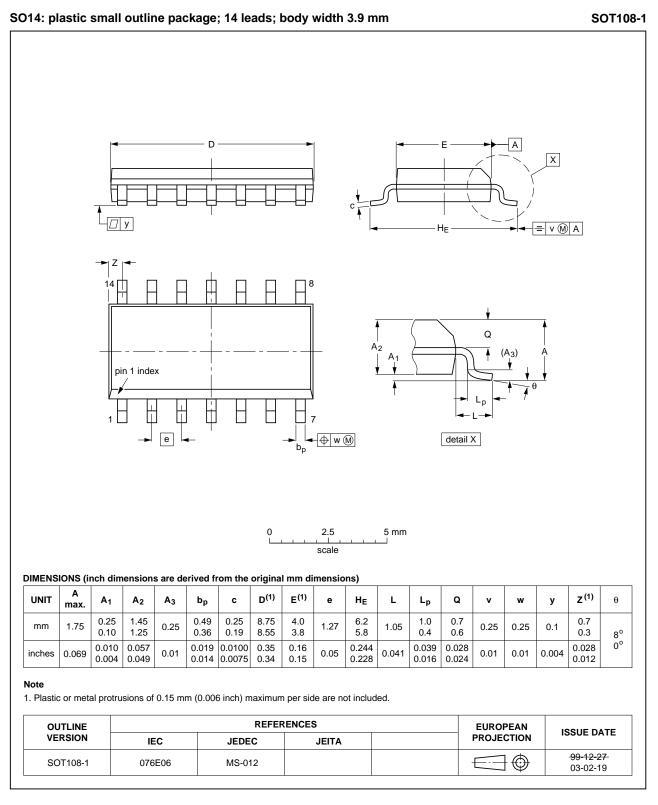


#### Table 9.Test data

Туре	Input L		Load	Test
	VI	t <sub>r</sub> , t <sub>f</sub>	CL	
74AHC00-Q100	V <sub>CC</sub>	$\leq$ 3.0 ns	15 pF, 50 pF	t <sub>PLH</sub> , t <sub>PHL</sub>
74AHCT00-Q100	3.0 V	≤ 3.0 ns	15 pF, 50 pF	t <sub>PLH</sub> , t <sub>PHL</sub>

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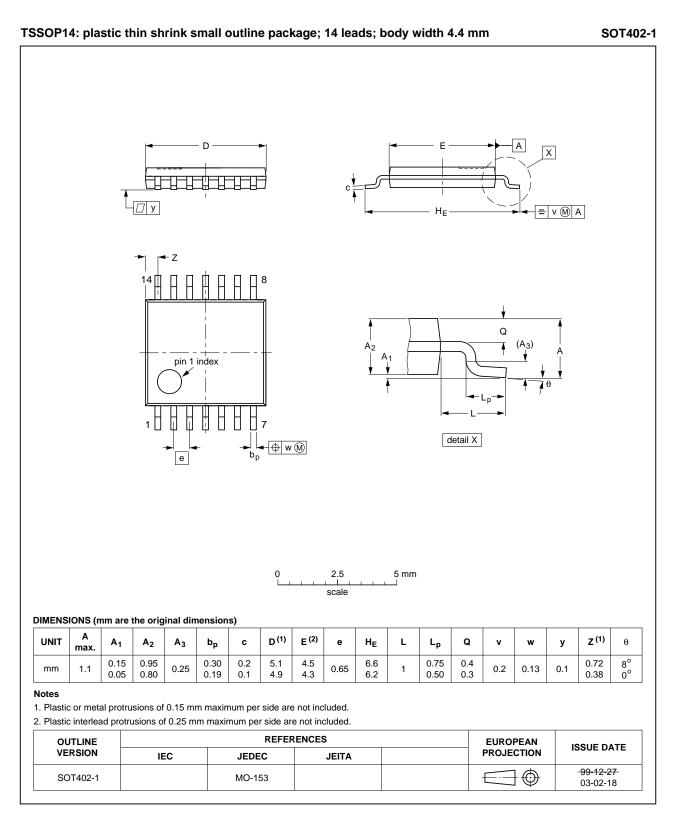
## 12. Package outline



### Fig 8. Package outline SOT108-1 (SO14)

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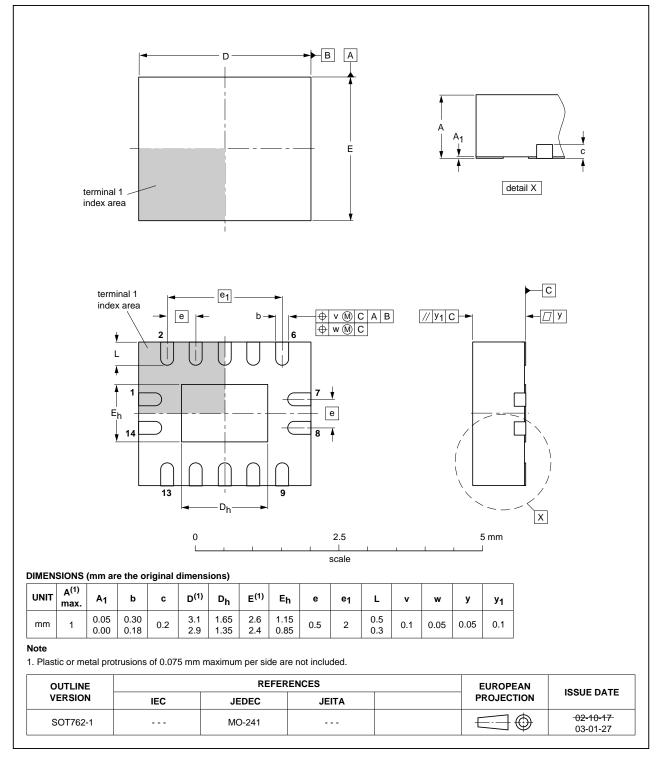
**Quad 2-input NAND gate** 



### Fig 9.Package outline SOT402-1 (TSSOP14)

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DHVQFN14: plastic dual in-line compatible thermal enhanced very thin quad flat package; no leads; 14 terminals; body 2.5 x 3 x 0.85 mm SOT762-1

#### Fig 10. Package outline SOT762-1 (DHVQFN14)

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## **13. Abbreviations**

Table 10. Abbreviations		
Acronym	Description	
CDM	Charge Device Model	
CMOS	Complementary Metal-Oxide Semiconductor	
DUT	Device Under Test	
ESD	ElectroStatic Discharge	
HBM	Human Body Model	
LSTTL	Low-power Schottky Transistor-Transistor Logic	
MIL	Military	
MM	Machine Model	
TTL	Transistor-Transistor Logic	

## 14. Revision history

### Table 11.Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes
74AHC_AHCT00_Q100 v.1	20130416	Product data sheet	-	-

## 15. Legal information

#### 15.1 Data sheet status

Document status[1][2]	Product status <sup>[3]</sup>	Definition
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